

# SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

# **FW217A** — General-Purpose Switching Device Applications

#### **Features**

- On-state resistance  $RDS(on)1=30m\Omega$  (typ.)
- · 4.5V drive
- · Halogen free compliance
- · Protection Diode in

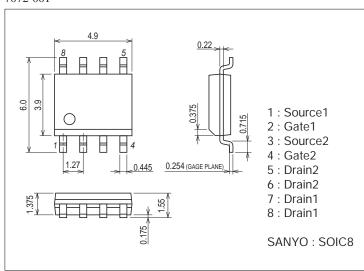
# **Specifications**

#### Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V <sub>DSS</sub>		35	V
Gate-to-Source Voltage	V <sub>GSS</sub>		±20	V
Drain Current (DC)	ID		6	Α
Drain Current (PW≤10s)	IDP	Duty cycle≤1%	6.5	А
Drain Current (PW≤10μs)	IDP	Duty cycle≤1%	24	А
Allowable Power Dissipation	PD	When mounted on ceramic substrate (2000mm²x0.8mm) 1unit, PW≤10s	1.8	W
Total Dissipation	PT	When mounted on ceramic substrate (2000mm²x0.8mm), PW≤10s	2.2	W
Channel Temperature	Tch		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### **Package Dimensions**

unit : mm (typ) 7072-001

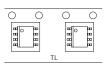


#### **Product & Package Information**

• Package : SOIC8

• JEITA, JEDEC : SC-87, SOT-96 • Minimum Packing Quantity : 2,500 pcs./reel

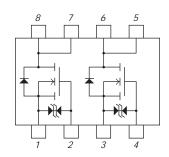
#### Packing Type: TL



# Marking



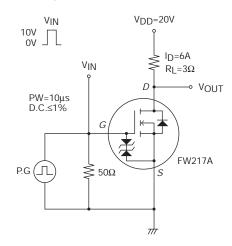
#### **Electrical Connection**

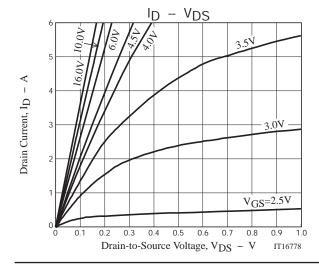


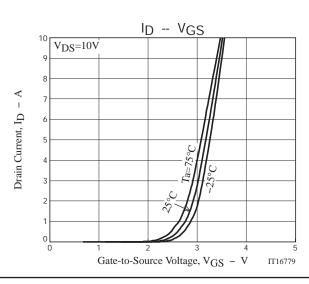
#### Electrical Characteristics at Ta=25°C

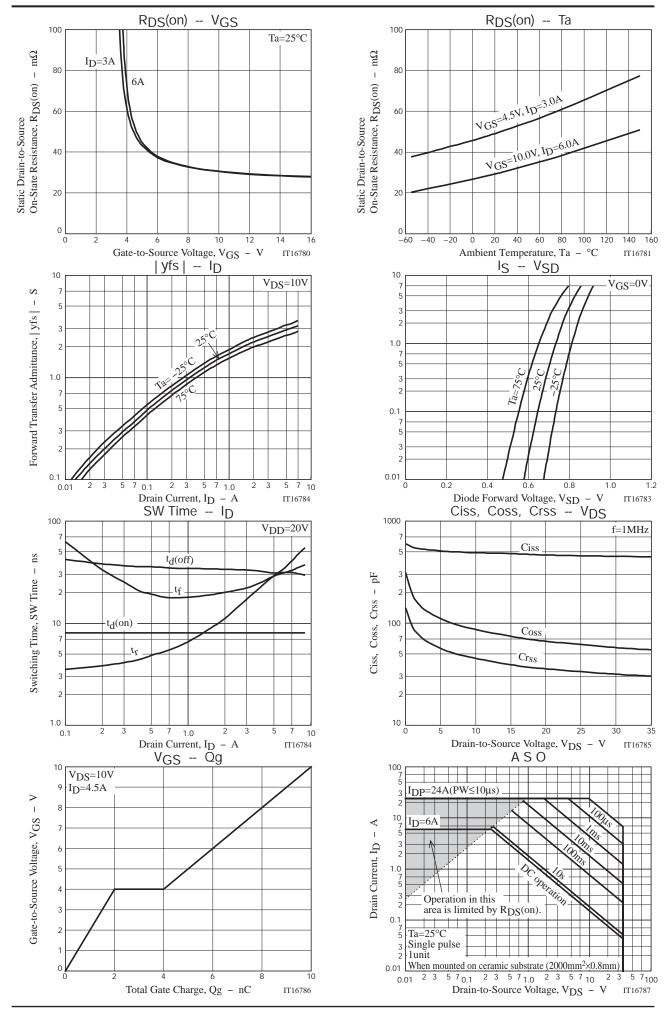
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	Ullit
Drain-to-Source Breakdown Voltage	V(BR)DSS	ID=1mA, VGS=0V	35			V
Zero-Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =35V, V <sub>GS</sub> =0V			1	μΑ
Gate-to-Source Leakage Current	IGSS	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μΑ
Cutoff Voltage	V <sub>GS</sub> (off)	V <sub>DS</sub> =10V, I <sub>D</sub> =1mA	1.7		2.6	٧
Forward Transfer Admittance	yfs	V <sub>D</sub> S=10V, I <sub>D</sub> =6A		3		S
Static Drain-to-Source On-State Resistance	R <sub>DS</sub> (on)1	I <sub>D</sub> =6A, V <sub>G</sub> S=10V		30	39	mΩ
	R <sub>DS</sub> (on)2	I <sub>D</sub> =3A, V <sub>G</sub> S=4.5V		50	70	mΩ
Input Capacitance	Ciss			470		pF
Output Capacitance	Coss	V <sub>DS</sub> =20V, f=1MHz		70		pF
Reverse Transfer Capacitance	Crss			35		pF
Turn-ON Delay Time	t <sub>d</sub> (on)			8		ns
Rise Time	t <sub>r</sub>	Con appointed Toot Circuit		34		ns
Turn-OFF Delay Time	t <sub>d</sub> (off)	See specified Test Circuit.		31		ns
Fall Time	tf			30		ns
Total Gate Charge	Qg			10		nC
Gate-to-Source Charge	Qgs	V <sub>DS</sub> =20V, V <sub>GS</sub> =10V, I <sub>D</sub> =6A		2		nC
Gate-to-Drain "Miller" Charge	Qgd			2		nC
Diode Forward Voltage	VSD	IS=6A, VGS=0V		0.84	1.2	V

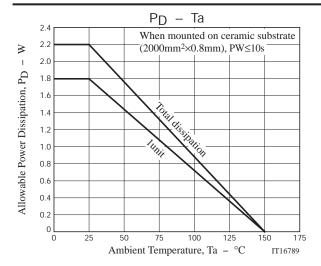
### **Switching Time Test Circuit**

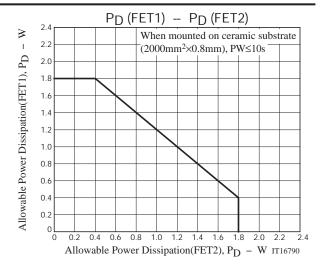












Note on usage: Since the FW217A is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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